

RoHS

HALOGEN FREE

GREEN

# High Speed Infrared Emitting Diodes, 850 nm, GaAlAs, DH

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#### **DESCRIPTION**

VSMG28511 series are infrared, 850 nm emitting diodes in GaAlAs (DH) technology with high radiant power and high speed, molded in clear, untinted plastic packages (with lens) for surface mounting (SMD).

#### **FEATURES**

Package type: surface mount





Peak wavelength: λ<sub>p</sub> = 850 nm

High reliability

• High radiant power

High radiant intensity

• Angle of half intensity:  $\varphi = \pm 12^{\circ}$ 

· Low forward voltage

- · Suitable for high pulse current operation
- Terminal configurations: Gullwing or reserve gullwing
- Package matches with detector VEMD2000X01 series
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>



- · Data transmission
- IR-illumination (CCTV)
- · Miniature light barrier
- Photointerrupters
- · Optical switch
- · Shaft encoders
- IR emitter source for proximity applications
- · Smoke detectors

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>p</sub> (nm)	t <sub>r</sub> (ns)	
VSMG285011RG	40	± 12	850	20	
VSMG285011G	40	± 12	850	20	

### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
VSMG285011RG	Tape and reel	MOQ: 6000 pcs, 6000 pcs/reel	Reverse gullwing		
VSMG285011G	Tape and reel	MOQ: 6000 pcs, 6000 pcs/reel	Gullwing		

#### Note

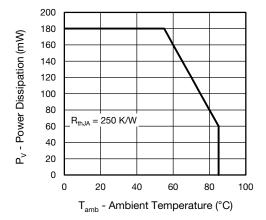
• MOQ: minimum order quantity



### www.vishay.com

# Vishay Semiconductors

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V <sub>R</sub>	5	V
Forward current		I <sub>F</sub>	100	mA
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	Α
Power dissipation		P <sub>V</sub>	180	mW
Junction temperature		Tj	100	°C
Operating temperature range		T <sub>amb</sub>	-40 to +85	°C
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C
Soldering temperature	Acc. figure 9, J-STD-020	T <sub>sd</sub>	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	250	K/W



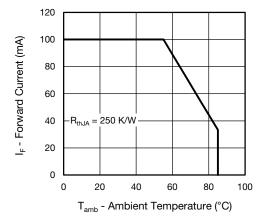


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

Fig. 2 - Forward Current Limit vs. Ambient Temperature

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Farmered maltage	$I_F = 100 \text{ mA}, t_p = 100 \mu\text{s}$	V <sub>F</sub>	1.25	1.5	1.8	V
Forward voltage	$I_F = 1 \text{ A, t}_p = 100 \mu\text{s}$	V <sub>F</sub>		2.9		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		-1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μΑ
Junction capacitance	$V_R = 0 \text{ V, f} = 1 \text{ MHz, E} = 0 \text{ mW/cm}^2$	CJ		45		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 100 \mu \text{s}$	I <sub>e</sub>	20	40	60	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	I <sub>e</sub>		320		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 100 \mu \text{s}$	фe		40		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 100 mA	TKφ <sub>e</sub>		-0.35		%/K
Angle of half intensity		φ		± 12		deg
Peak wavelength	I <sub>F</sub> = 30 mA	$\lambda_{p}$	830	850	870	nm
Spectral bandwidth	I <sub>F</sub> = 30 mA	Δλ		35		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 30 mA	TKλ <sub>p</sub>		0.25		nm/K
Rise time	I <sub>F</sub> = 100 mA, 20 % to 80 %	t <sub>r</sub>		20		ns
Fall time	I <sub>F</sub> = 100 mA, 20 % to 80 %	t <sub>f</sub>		20		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f <sub>c</sub>		23		MHz

### **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

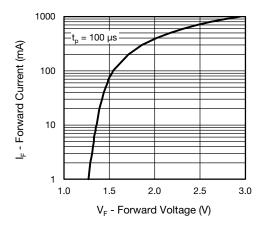


Fig. 3 - Forward Current vs. Forward Voltage

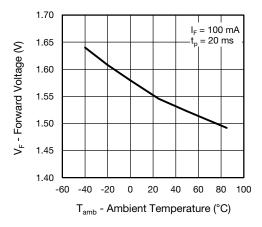


Fig. 4 - Forward Voltage vs. Ambient Temperature

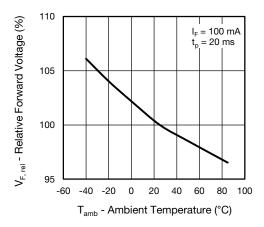


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

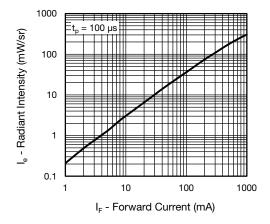


Fig. 6 - Radiant Intensity vs. Forward Current

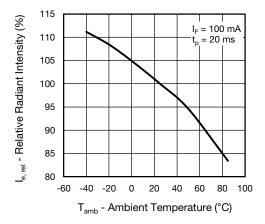


Fig. 7 - Relative Radiant Intensity vs. Ambient Temperature

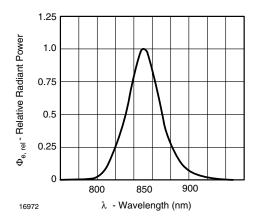


Fig. 8 - Relative Radiant Power vs. Wavelength

## VSMG285011RG, VSMG285011G

### Vishay Semiconductors

### **DRYPACK**

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

#### **FLOOR LIFE**

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

Conditions:  $T_{amb}$  < 30 °C, RH < 60 %

Moisture sensitivity level 2a, acc. to J-STD-020.

### **DRYING**

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.

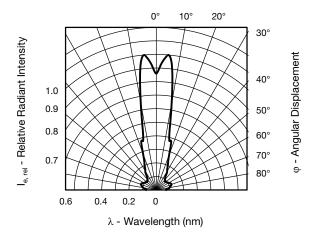


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

### **SOLDER PROFILE**

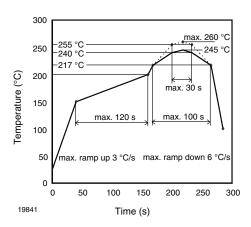
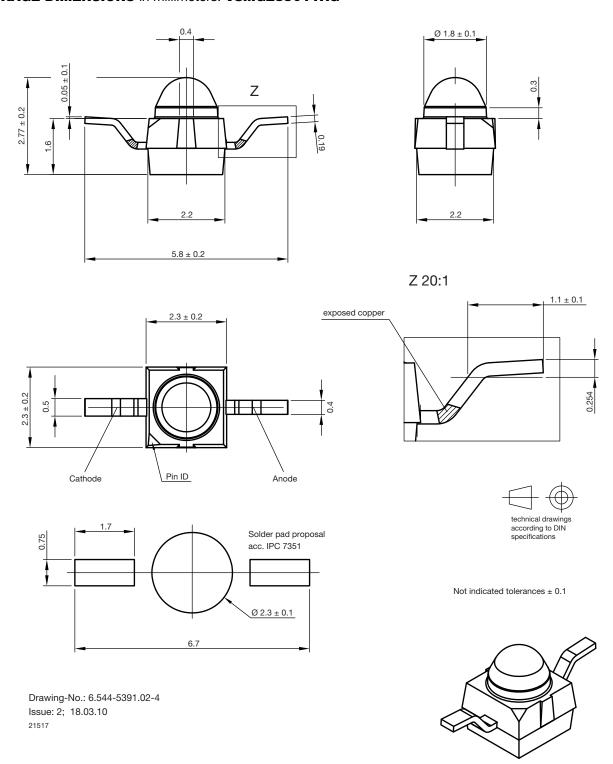


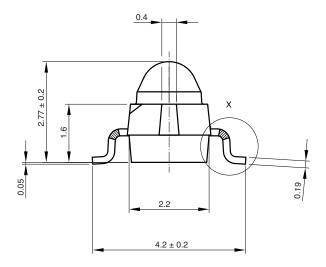
Fig. 10 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

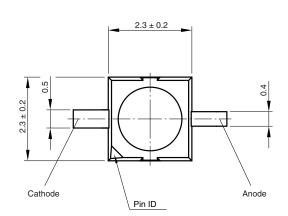
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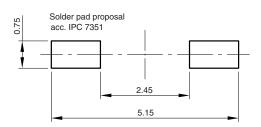
### PACKAGE DIMENSIONS in millimeters: VSMG285011RG



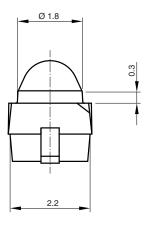
### PACKAGE DIMENSIONS in millimeters: VSMG285011G

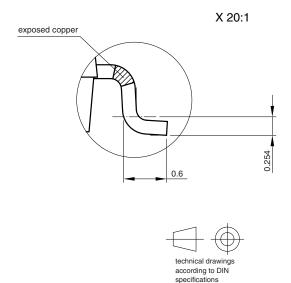


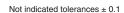


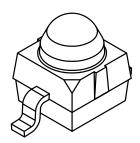


Drawing-No.: 6.544-5383.02-4 Issue: 4; 18.03.10



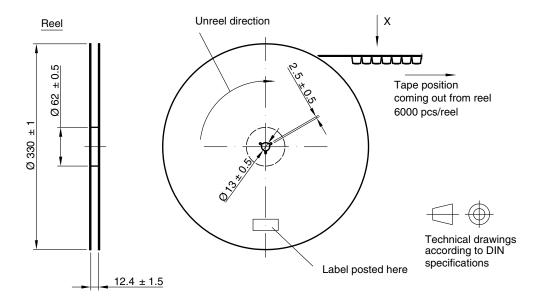




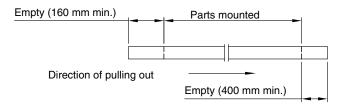




### TAPING AND REEL DIMENSIONS in millimeters: VSMG285011RG

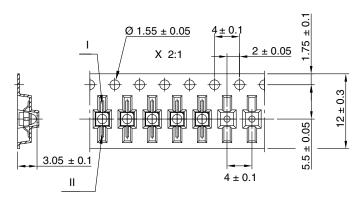


Leader and trailer tape:



### Terminal position in tape

Devicce	Lead I	Lead II
VEMT2000		
VEMT2500	Collector	Emitter
VEMD2000		
VEMD2500	0-4	AI -
VSMB2000	Cathode	Anode
VSMG2000		
VSMY2850RG	Anode	Cathode



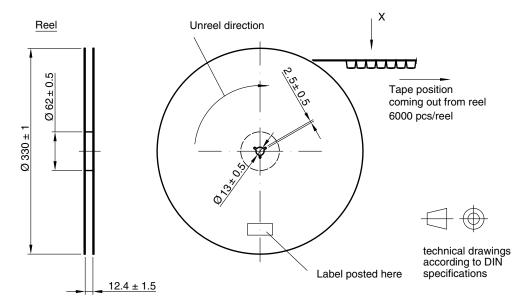
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Issue: 2; 18.03.10

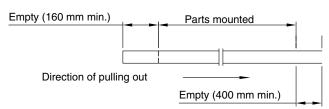
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### TAPING AND REEL DIMENSIONS in millimeters: VSMG285011G

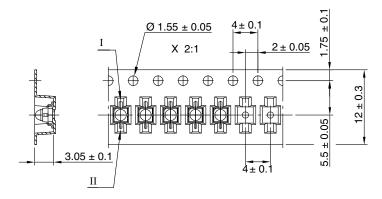


### Leader and trailer tape:



### Terminal position in tape

Devicce	Lead I	Lead II
VEMT2020		
VEMT2520	Collector	Emitter
VSMB2020		
VSMG2020	0-44-	Al -
VEMD2020	Cathode	Anode
VEMD2520		
VSMY2850G	Anode	Cathode



Drawing-No.: 9.800-5091.01-4

Issue: 3; 18.03.10

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